

# **COLLEGE OF ENGINEERING PUTRAJAYA CAMPUS FINAL EXAMINATION**

# **SEMESTER 1 2015 / 2016**



### **INSTRUCTIONS TO CANDIDATES:**

- 1. This paper contains **FIVE** (5) questions in **NINE** (9) pages.
- 2. Answer **ALL** questions.
- 3. Write **all** answers in the answer booklet provided. **Use pen** to write your answer.
- 4. Write answer to different question on **a new page**.

### *THIS QUESTION PAPER CONSISTS OF NINE* **(9)** *PRINTED PAGES INCLUDING THIS COVER PAGE.*

#### **Question 1 [20 marks]**

**Figure 1** has the transistor parameters of  $\beta$  = 180,  $V_{BE}(\text{on})$  = 0.7 V (for all transistors **EXCLUDING**  $Q_4$ ),  $V_A = \infty$  for  $Q_1$  and  $Q_2$ , and  $V_A = 100$  V for  $Q_3$  and  $Q_4$ .



**Figure 1**

- (a) **Calculate**  $R_1$  and  $R_2$  as such  $I_1 = 0.5$  mA and  $I_Q = 140 \mu\text{A}$ . [5 marks]
- (b) **Determine** the common-mode input resistance, *Ricm*, of the differential amplifier.

[10 marks]

(c) **Find** the common-mode voltage gain,  $A_{cm}$ , of the differential amplifier for  $R_C = 50 \text{ k}\Omega$ . The equation is given as  $\overline{a} = \overline{a} \overline{R}$  [5 marks]  $A_{cm} = \frac{-g_m R}{2(1+R)}$  $m^{11}C$ 

$$
_{cm}=\frac{-g_{m}R_{C}}{1+\frac{2(1+\beta)R_{o}}{r_{\pi}}}
$$

#### Q1 Answer

(a) Calculate  $R_1$  and  $R_2$  as such  $I_1 = 0.5$  mA and  $I_Q = 140 \mu A$ . Using the KVL rule, [5 marks]

$$
I_1 = \frac{10 - 0.7 - (-10)}{R_1} = 0.5m \,[1.5]
$$
  

$$
R_1 = \frac{38.60 \,\mathrm{k}}{1}
$$

For the Widlar & current source,

$$
I_{O}R_{E}=V_{\rm T}\ln\left(\frac{t_{KBF}}{t_{O}}\right)[1.5]
$$

Substituting for *R2*,

$$
I_0 R_E = V_T \ln \left(\frac{I_{REF}}{I_0}\right)
$$
  
\n
$$
R_E = \frac{V_T}{I_0} \ln \left(\frac{I_{REF}}{I_0}\right)
$$
  
\n
$$
R_Z = \frac{V_T}{I_0} \ln \left(\frac{I_{REF}}{I_0}\right) = \frac{0.026}{0.14} \ln \left(\frac{0.5m}{0.14m}\right) = 236 \Omega [1]
$$

(b) Determine the common-mode input resistance, *Ricm*.

[10 marks]

$$
R_{icm} \approx (1+\beta)R_o
$$
 [2]

For Widlargs current source,  $R_0 - r_{04} (1 + g_{m4} R_E^t)$  [2]

$$
g_{m4} = \frac{lq}{v_T} = \frac{0.14m}{0.026} = 5.385 \ mA/V \ [1]
$$
\n
$$
r_{m4} = \frac{\beta v_T}{l_Q} = \frac{(180)(0.026)}{0.14m} = 33.40 \ k\Omega \ [1]
$$
\n
$$
R_E' = r_{m4} || R_2 = 0.234 \ k\Omega \ [1]
$$
\n
$$
r_{04} = \frac{v_A}{l_Q} = \frac{100}{0.14m} = 714 \ k\Omega \ [1]
$$

Substituting into the main equation,

$$
R_o = 714k(1 + (5.385)(0.234k)) = 1614 k\Omega [1]
$$
  
 
$$
\therefore R_{lcm} = (180 + 1)1614k \approx 292M\Omega [1]
$$

(c) Find the common-mode voltage gain,  $A_{cm}$ , for  $R_C = 50 \text{ k}\Omega$ . [5 marks]

$$
Given A_{cm} = \frac{-g_m R_c}{1 + \frac{2(1+\beta)R_o}{r_{\pi}}}
$$

$$
g_{m1} = \frac{l_Q}{v_T} = \frac{0.14m/2}{0.026} = \frac{0.07m}{0.026} = 2.692 \text{ mA/V} \text{ [2]}
$$
  
\n
$$
r_{m1} = \frac{\beta v_T}{l_Q} = \frac{(180)(0.026)}{0.14m/2} = 66.86 \text{ k}\Omega \text{ [2]}
$$
  
\nSubstituting these into the equation,  
\n
$$
A_{cm} = \frac{-(2.692m)(60k)}{1 + \frac{2(1 + 180)(1648k)}{66.86k}} = -0.0154 \text{ [1]}
$$

#### **Question 2 [20 marks]**

For the differential amplifier **with 2-transistor active load** circuits in **Figure 2** it is given that the circuit parameters are:  $V^+=10$  V,  $V^-=-10$  V, and  $I_Q=0.1$  mA.

**NMOS** transistor parameters are:  $V_{TN} = 1$  **V**,  $k'_{n} = 80 \mu A/V^{2}$ , and  $\lambda_{n} = 0.01$  **V**<sup>-1</sup>; and the **PMOS** transistor parameters are:  $V_{TP} = -1 \text{ V}$ ,  $k_p^* = 40 \mu\text{A/V}^2$ , and  $\lambda_p = 0.015 \text{ V}^{-1}$ .





(a) **Find** the differential gain  $A_d$ , given  $(W/L)_1 = (W/L)_2 = 2$  and  $(W/L)_3 = (W/L)_4 = 4$ .

[5 marks]

- (b) **Redesign** the differential pair  $M_1$  and  $M_2$  if the value of the gain is **to be increased 5 times** than that calculated in **part (a)**. [6 marks]
- (c) It is given that the **constant current source**  $I_Q$  is implemented with a two-transistor current source with  $(W/L) = 5$  for the transistors. **Sketch** the differential amplifier circuit **together** with the two-transistor current source. Then, **calculate** the value of the minimum common-mode input voltage,  $V_{cm}(\text{min})$  of the differential pair. [9 marks]

### Q2 Answer

Question 2(a) [5 marks]  
\n
$$
A_d = g_{m1}(r_{o2}||r_{o4})
$$
 [2]  
\n $I_{D1} = I_Q/2 = I_{D2} = I_{D3} = I_{D4} = 0.1mA/2 = 0.05mA$   
\n $g_{m1} = 2\sqrt{K_n I_{D1}} = 2\sqrt{\frac{k_n}{2} \left(\frac{W}{L}\right) I_{D1}} = 2\sqrt{\frac{80}{2} \left(2\right)(0.05m)} = 0.1265mA/V$  [1]  
\n $r_{o2} = \frac{1}{\lambda_n I_{D2}} = \frac{1}{(0.01)(0.05m)} = 2M\Omega$  [0.5]  
\n $r_{o4} = \frac{1}{\lambda_p I_{D4}} = \frac{1}{(0.015)(0.05m)} = 1.33M\Omega$  [0.5]  
\n $A_d = (0.1265m)(2M || 1.33M) = 101V/V$  [1]

Question 2(b) [6 marks]  
\n
$$
A_{dNew} = 5 \times A_d = 5 \times 101 = 505V/V
$$
 [1]  
\n $A_{dNew} = g_{m1New} (r_{o2} || r_{o4})$   
\n $505 = g_{m1New} (0.79M)$  [2]  
\n $g_{m1New} = 0.6395mA/V$  [1]  
\n $g_{m1New} = 2\sqrt{\frac{k_n}{2} \left(\frac{W}{L}\right)_{1New}} I_{D1} = 2\sqrt{\left(\frac{80}{2} \right) \left(\frac{W}{L}\right)_{1New}} (0.05m)$   
\n $0.6395m = \sqrt{\left(\frac{W}{L}\right)_{1New}} (8.94 \times 10^{-5})$  [1]  
\n $\left(\frac{W}{L}\right)_{1New} = 51.1$  [1]

#### Question 2(c) [9 marks]

Diagram [1]



$$
Q2(c)
$$

 $(V_{GS1} - V_{TN})$  $(2)(V_{GS1}-1)$  $(V_{GSS} - V_{TN})$  $(5)(V_{GSS} - 1)$  $V_{DS}(sat) = V_{GS5} - V_{TN} = 1.707 - 1 = 0.707V$  [1]  $\rightarrow$   $V_{GSS}$  = 1.707*V* [2] 2  $0.1m = \left(\frac{80}{2}\right)(5)(V_{csc} - 1)^2$ 2  $;V_{D5}(sat)$  $\rightarrow$   $V_{GS1} = 1.791V$  [2] 2  $0.05m = \left(\frac{80}{2}\right)(2)(V_{GS1} - 1)^2$ 2  $;V_{GS1}$  $V_{cm}(\text{min}) = V_{GS1} + V_{DS}(sat) + V^{-}$  [2]  $m = \left(\frac{80}{2}\right) (5) (V_{GSS} -$ 2 5 5 '  $S_5 = I_Q = \frac{K_n}{2} \left| \frac{V}{I} \right| V_{GSS} - V_Q$  $m = \left(\frac{80}{2}\right) (2) (V_{GS1} -$ 2 1 1 '  $v_1 = \frac{\kappa_n}{2} \left| \frac{V}{I} \right| \left| \left| V_{GS1} - V \right| \right|$ *L*  $I_{DS} = I_Q = \left(\frac{k_n}{2}\right)\left(\frac{W}{I}\right)\left(V_{GSS} - V_{TN}\right)$ *L*  $I_{D1} = \left(\frac{k_n}{2}\right)\left(\frac{W}{I}\right)\left(V_{GSI} - V_{TN}\right)$ *n*  $I_{D5} = I_{Q} = \left(\frac{k_{n}}{2}\right)\left(\frac{W}{L}\right)_{5}\left(V_{GSS}$ *n*  $L_{D1} = \left(\frac{k_n}{2}\right)\left(\frac{W}{L}\right)_{1} \left(V_{GS1} - \right)$  $\setminus$  $=$  $\setminus$ Ê  $\sqrt{ }$  $\overline{\phantom{a}}$ ˆ Á Á  $\setminus$  $= I_{\Omega} = \left($  $\setminus$  $=$  $\setminus$ Ê  $\sqrt{ }$  $\overline{\phantom{a}}$ ˆ Á Á  $\setminus$  $=$ 

 $V_{cm}$ (min) = 1.791 + 0.707 + (-10) = -7.5V [1]

#### **Question 3 [20 marks]**

- (a) Please **refer** to the multistage amplifier circuit shown in **Figure 3**. **Calculate** the smallsignal input impedance of the gain stage indicated by  $R_i$ <sup>2</sup>. It is given that current  $I_{R4} = 0.4$ **mA**, and for the transistors  $\beta$  = **200** and  $V_A$  = **100 V**. [4 marks]
- (b) Refer to **Figure 3** also. If the gain of the differential amplifier:  $A_{d1} = v_{02}/v_d$ , the gain of the gain stage:  $A_{\nu2} = v_{\nu3}/v_{\nu2}$ , and the gain of the output stage:  $A_{\nu2} = v_{\nu}/v_{\nu3}$ ,
	- (i) Express  $A_{vtotal}$ , i.e. the overall gain of the op-amp circuit in terms of  $A_{d1}$ ,  $A_{\nu2}$  and  $A_{\nu 3}$ . [2 marks]
	- (ii) How does value of  $\mathbf{R}_{i2}$  calculated in **part (a)** affects the gain  $A_{d1}$ . [2 marks]



**Figure 3**

(c) **Figure 4** shows the **Class-AB** output stage circuit. Assume that  $V_{CC} = 10 \text{ V}$ ,  $V_{BB} = 1.35 \text{ V}$ , and  $R_L = 1$  **k** $\Omega$ . Transistors  $Q_n$  and  $Q_p$  are matched, with  $I_s = 4 \times 10^{-15}$  **A**. It is given that output voltage  $v_0 = -8$  V. Calculate the voltages  $v_{BEN}$ ,  $v_{EBP}$ , and input voltage  $v_I$ , as well as currents  $i_L$ ,  $i_{Cn}$ , and  $i_{Cp}$ . Then **calculate** the power dissipated in the transistors  $P_{Qn}$  and  $P_{Qp}$ .

[12 marks]



**Figure 4**

#### Q3 Answer

Question 3(a) [4 marks]  
\n*R<sub>i2</sub> = r<sub>π3</sub> + (1 + β)r<sub>π4</sub> [1.5]  
\n*I<sub>E4</sub> = I<sub>R4</sub> = 0.4 mA*  
\n*I<sub>C4</sub> = 
$$
\frac{\beta}{1 + \beta}
$$
 *I<sub>E4</sub> =  $\frac{200}{201}(0.4m) = 0.398mA$*   
\n*r<sub>π4</sub> =  $\frac{\beta V_T}{I_{C4}} = \frac{(200)(26m)}{0.398m} = 13.07kΩ$  [0.5]  
\n[*r<sub>π4</sub> = 13kΩ* with *I<sub>C4</sub> ≅ I<sub>E4</sub>* is also okay]  
\n*I<sub>E3</sub> = I<sub>B4</sub> =  $\frac{I_{E4}}{1 + \beta}$*   
\n*I<sub>C3</sub> =  $\frac{\beta}{1 + \beta}$  *I<sub>E3</sub> =  $\frac{\beta}{(1 + \beta)} \frac{I_{E4}}{(1 + \beta)} = \frac{200}{(201)^2}(0.4m) = 1.98 \times 10^{-6} A$  [0.5]  
\n*r<sub>π3</sub> =  $\frac{\beta V_T}{I_{C3}} = \frac{(200)(26m)}{1.98 \times 10^{-6}} = 2.63MΩ$  [0.5]  
\n∴ *R<sub>i2</sub> = (2.63M) + (201)(13.07k) = 5.26MΩ* [1]******

Question 3(b) [4 marks] (i)  $A_{vTOTAL} = V_0/V_d = A_{d1} x A_{v2} x A_{v3}$  [2]

(ii) The value of Ri2 is very large, hence the input impedance of the  $2<sup>nd</sup>$  gain stage will not load down or decrease the gain of the  $1<sup>st</sup>$  stage, Ad1. I.e. the loading effect of the  $2<sup>nd</sup>$ stage onto the  $1<sup>st</sup>$  stage can be neglected. [2]

Question 3(c) [12 marks]

For  $v_0 = -8$  V,  $i_L$  =  $V_O / R_L$  =  $(-8V)/(1 k\Omega)$  =  $-8 \text{ mA}$  [1]

Therefore,  $Q_p$  is conducting and  $Q_n$  is OFF.

**Approximation:** 

$$
i_{Cp} \approx |i_L| = 8 \text{ mA}
$$
 [1]  
\n
$$
v_{EBp} = V_T \ln(i_{Cp} / I_S)
$$
  
\n
$$
= (0.026) \ln(8\text{m} / 4 \times 10^{-15}) = 0.7364 \text{ V}
$$
 [1]  
\n
$$
v_{BEn} = V_{BB} - v_{EBp} = 1.35 - 0.7364 = 0.6136 \text{ V}
$$
 [1]  
\n
$$
V_{In} = V_O + V_{BB}/2 - v_{EBp} = -8 + 1.35/2 - 0.7364 = -8.06 \text{ V}
$$
 [1]  
\n
$$
i_{Cn} = I_S \exp(V_{BEn} / V_T)
$$
  
\n
$$
= (4 \times 10^{-15}) \exp(0.6136 / 0.026) = 7.102 \times 10^{-5} \text{ A}
$$
 [1]  
\n
$$
i_{Cn} = i_{Cp} + i_L
$$
 [1]  
\n
$$
i_{Cp} = i_{Cn} - i_L
$$
 Recalculate  $i_{Cp}$   
\n
$$
= 7.102 \times 10^{-5} - (-8 \text{ m}) = 8.071 \text{ mA}
$$
 [1]

**For** *Qn***:**

$$
V_{CEn} = V_{CC} - V_0 = 10 - (-8) = 18 \text{ V}
$$
 [0.5]

$$
P_{Qn} = i_{Cn} V_{CEn} = (7.102 \times 10^{-5})(18) = 1.278 \text{ mW} \qquad [0.5]
$$
  
[1]

For  $Q_p$ :  $V_{ECp}$  =  $V_0$  –  $(-V_{CC})$  =  $(-8)$  –  $(-10)$  = 2 V **[0.5]**  $P_{Qp}$  =  $i_{Cp}$  *v<sub>ECp</sub>* = (8.071m)(2) = 16.14 mW [0.5] **[1]**

#### **Question 4 [20 marks]**

Consider a **standard 741 operational amplifier** (op-amp) circuit as shown in **Figure 5**. Study Figure 5 carefully and observe the output stage of the operational amplifier. Assume load resistance connected to the <u>Output of the 741 op-amp</u> is  $R_L = 2$  k $\Omega$ .

The op-amp is supplied by  $\pm$ 5 V DC voltages. The transistors have  $\beta_n = 200$ ,  $\beta_p = 50$ ,  $V_{AN} = V_{AP}$  $= 50 \text{ V}$ ,  $V_{BE}(\text{on}) = V_{EB}(\text{on}) = 0.6 \text{ V}$ , and the reverse saturation currents  $I_{S18} = I_{S19} = 2 \times 10^{-14} \text{ A}$ , and  $I_{S14} = I_{S20} = 5 \times 10^{-14}$  A.

From DC analysis, bias currents <u>for selected transistors</u> are  $I_{C13A} = 0.125$  mA,  $I_{C13B} = 0.375$ **mA**,  $I_{C19} = 0.113$  mA. Determine the output stage quiescent currents  $I_{C14}$  and  $I_{C20}$ . Analyse the **changes** in output current  $i_{C20}$  if  $i_{C14} = 1$  mA. Please state the class of this output stage.

This output stage includes a number of transistors that are  $\tilde{\text{co}}$  ffö during the normal operation. By providing example, **identify and discuss** the functional operation of these transistors when they are **<u>oono.</u>** [20 marks]



**Figure 5**

### Q4 Answer [20 marks]

$$
V_{BE19} = V_T \ln (I_{C19}/I_{S19}) = 0.026 \ln (0.113 \text{m}/2\text{E} - 14) = 0.58383 \text{ V}
$$
 [1.5]  
\n
$$
I_{C18} = I_{B19} + (I_{R10}) = (I_{C19}/ ) + (V_{BE19}/R_{10})
$$
  
\n
$$
= (0.113 \text{m}/200) + (0.58383/50 \text{ k}) = 12.242 \mu \text{A}
$$
 [3]  
\n
$$
V_{BE18} = V_T \ln (I_{C18}/I_{S18}) = 0.026 \ln (12.242 \mu/2\text{E} - 14) = 0.52604 \text{ V}
$$
 [1.5]  
\n
$$
V_{BB} = V_{BE18} + V_{BE19} = 0.52604 + 0.58383 = 1.1099 \text{ V}
$$
 [1.5]  
\n
$$
V_{BE14} = V_{BE20} = V_{BB}/2 = 1.1099/2 = 0.5549 \text{ V}
$$
 [1]  
\n
$$
I_{C14} = I_{C20} = I_S \exp [V_{BE}/V_T] = (5E-14) \exp[0.5549/0.026] = 92.99 \mu \text{A}
$$
 [2.5]



## **Keywords:**

short circuit protection circuitry; when  $R_L$  is shorted 6 large current in  $Q_{14}$  during positive input cycle;  $R_6$  and  $Q_{15}$  limits short circuit current in  $Q_{14}$  [5]

### **OR**

short circuit protection circuitry; when  $R_L$  is shorted 6 large current in  $Q_{20}$  during negative input cycle;  $R_7$ ,  $Q_{21}$  and  $Q_{24}$  limits short circuit current in  $Q_{20}$ .

#### **Question 5 [20 marks]**

- (a) With an **input resistor**  $(R_1)$  of 50 k $\Omega$ , design an amplifier using op-amp with a **closedloop gain** of **25 V/V. Draw and label clearly** your circuit design. [4 marks]
- (b) Consider the two inverting op-amp circuit connected in cascade as shown in **Figure 6**. Let  $R_1 = 25 \text{ k}\Omega$ ,  $R_2 = 100 \text{ k}\Omega$ ,  $R_3 = 80 \text{ k}\Omega$ , and  $R_4 = 50 \text{ k}\Omega$ . Calculate  $v_0/v_I$  for the circuit. [4 marks]



**Figure 6**

(c) **Figure 7** in the following page shows a design for an **instrumentation amplifier with variable differential voltage gain** using op-amps. In the design, *R***1***POT* is a **potentiometer** (or a variable resistor) used **to provide variable resistance** so that differential voltage gain  $(A<sub>v</sub>)$  of the instrumentation amplifier can be adjustable. With analysis, it can be shown that output voltage ( $v_0$ ) for the **difference amplifier** constructed using op-amp  $A_3$ , resistors  $R_3$ , and resistors *R***<sup>4</sup>** is

$$
v_O = \frac{R_4}{R_3} (v_{O2} - v_{O1})
$$



**Figure 7**

**(i) Study Figure 7 carefully**. Using same labels for all resistors, voltages and currents given in the **Figure 7**, show that the output voltage  $(v<sub>0</sub>)$  of the **instrumentation amplifier with variable differential voltage gain** is [8 marks]

$$
v_O = \frac{R_4}{R_3} \left( 1 + \frac{2R_2}{R_{1f} + R_{1POT}} \right) (v_{I2} - v_{I1})
$$

(ii) For the circuit in Figure 7, given that  $R_4 = 2 R_3$ ,  $R_2 = 495 \text{ k}\Omega$ ,  $R_{1f} = 10 \text{ k}\Omega$ ,  $R_{1POT}$ is set at 40 ká,  $v_{I1} = 0.90$  V, and  $v_{I2} = 1.25$  V. Calculate  $A_v$  and  $v_O$ .

[4 marks]

#### **-END OF QUESTION PAPER-**

## Q5 Answer

Question 5(a) [4 marks]

$$
A_v = v_0 / v_1 = 1 + (R_2/R_1)
$$
 [1]  
25 = 1 + (R<sub>2</sub>/50k)  $R_2 = 1200$  ká [1]  
Drawing: [2]

 $R_1 = 50$  ká,  $R_2 = 1200$  ká, correct op-amp symbol, GND,  $v_O$ , and  $v_I$ 



Question 5(b) [4 marks]  
\n
$$
v_O = (-R_4/R_3)v_{O1}
$$
 [1]  
\n
$$
v_{O1} = (-R_2/R_1)v_I
$$
 [1]  
\n
$$
v_O = (-R_4/R_3)(-R_2/R_1)v_I
$$
 [1]  
\n
$$
v_O / v_I = (R_4/R_3)(R_2/R_1)
$$
  
\n
$$
= [(50k/80k)(100k/25k)] = 2.5 \text{ V/V}
$$
 [1]

Question  $5(c)(i)$  [8 marks]

$$
i_1 = \frac{v_{I1} - v_{I2}}{R_{1f} + R_{1POT}} [1]
$$
  
\n
$$
v_{O1} = v_{I1} + i_1 R_2 = \left(1 + \frac{R_2}{R_{1f} + R_{1POT}}\right) v_{I1} - \frac{R_2}{R_{1f} + R_{1POT}} v_{I2} [2]
$$
  
\n
$$
v_{O2} = v_{I2} - i_1 R_2 = \left(1 + \frac{R_2}{R_{1f} + R_{1POT}}\right) v_{I2} - \frac{R_2}{R_{1f} + R_{1POT}} v_{I1} [2]
$$
  
\n
$$
v_O = \frac{R_4}{R_3} (v_{O2} - v_{O1}) [1]
$$
  
\n
$$
v_O = \frac{R_4}{R_3} \left(1 + \frac{2R_2}{R_{1f} + R_{1POT}}\right) (v_{I2} - v_{I1}) [2]
$$

Question  $5(c)(ii)$  [4 marks]

$$
A_{\nu} = \frac{v_O}{(v_{I2} - v_{I1})} = \frac{R_4}{R_3} \left( 1 + \frac{2R_2}{R_{1f} + R_{1POT}} \right)
$$
 [1]  
\n
$$
A_{\nu} = \frac{2R_3}{R_3} \left( 1 + \frac{2(495k)}{10k + 40k} \right) = 41.6 \text{ V/V} \qquad [1]
$$
  
\n
$$
v_O = \frac{R_4}{R_3} \left( 1 + \frac{2R_2}{R_{1f} + R_{1POT}} \right) (v_{I2} - v_{I1}) \qquad [1]
$$
  
\n
$$
v_O = A_{\nu} (v_{I2} - v_{I1}) = (41.6)(1.25 - 0.90) = 16.224 \text{ V} \qquad [1]
$$

#### **APPENDIX:**

### **A)** BASIC FORMULA FOR TRANSISTOR

BJT MOSFET  $= I_s e^{v_{EB}/V_T}$ ; PNP  $= I_s e^{v_{BE}/V_T}$ ; NPN  $i_C = I_S e^{v_{EB}/V_T}$  $i_C = I_S e^{v_{BE}/V_T}$ 

$$
i_C = \beta i_B = \alpha i_E
$$
  

$$
i_E = i_B + i_C
$$
  

$$
\alpha = \frac{\beta}{\beta + 1}
$$

;Smallsignal

*I*

*T*

*CQ*

=

*g*

 $m - \overline{V}$ 

 $\beta = g_m r_{\pi}$ 

; N - MOSFET  
\n
$$
v_{DS}
$$
(sat) =  $v_{GS} - V_{TN}$   
\n $i_D = K_n[v_{GS} - V_{TN}]^2$   
\n $K_n = \frac{\mu_n C_{ox} W}{2L} = \frac{k_n}{2} \cdot \frac{W}{L}$ 

$$
; \mathbf{P}-\text{MOSFET}
$$
  
\n
$$
v_{SD}(\text{sat}) = v_{SG} + V_{TP}
$$
  
\n
$$
i_D = K_p[v_{SG} + V_{TP}]^2
$$
  
\n
$$
K_p = \frac{\mu_p C_{ox} W}{2L} = \frac{k_p}{2} \cdot \frac{W}{L}
$$

$$
r_{\pi} = \frac{\beta V_T}{I_{CQ}}
$$
  
\n
$$
r_o = \frac{V_A}{I_{CQ}}
$$
  
\n
$$
V_T = 26 \text{ mV}
$$
  
\n
$$
r_o \approx \frac{1}{\lambda I_{DQ}}
$$
  
\n
$$
r_o \approx \frac{1}{\lambda I_{DQ}}
$$

#### **B)** HYBRID- EQUIVALENT CIRCUITS  $\frac{D}{4}$ **B**  $V_{gs}$  $I_d$  $\leftrightarrow$   $g_m V_{gs} \ge r_o$  $V_{ds}$  $\triangleright_{g_m} v_{\pi} \xi_{r_o}$  $V_{\pi} \sum r_{\pi}$  $\overline{\mathbf{r}}$  $V_{ce}$  $\left( \mathrm{E}\right)$ S